

PNP Medium Power Transistor (Switching)

UMT4403 / SST4403 / MMST4403 / 2N4403

●Features

- 1) $BV_{CEO} < -40V$ ($I_c = 1mA$)
- 2) Complements the UMT4401 / SST4401 / MMST4401 / 2N4401.

●Package, marking, and packaging specifications

Pat No.	UMT4403	SST4403	MMST4403	2N4403
Pakaging type	UMT3	SST3	SMT3	TO-92
Marking	R2T	R2T	R2T	—
Code	T106	T116	T146	T93
Basic ordering unit (pieces)	3000	3000	3000	3000

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-40	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_c	-0.6	A
Collector power dissipation	UMT4403	0.2	W
	SST4403		
	MMST4403	0.625	
	2N4403		
Junction temperature	T_J	150	$^\circ C$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ C$

●External dimensions (Units : mm)

UMT4403

ROHM : UMT3
EIAJ : SC-70

(1) Emitter
(2) Base
(3) Collector

SST4403

ROHM : SST3

(1) Emitter
(2) Base
(3) Collector

MMST4403

ROHM : SMT3
EIAJ : SC-59

(1) Emitter
(2) Base
(3) Collector

2N4403

ROHM : TO-92
EIAJ : SC-43

(1) Emitter
(2) Base
(3) Collector

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-40	—	—	V	$I_c = -100 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-40	—	—	V	$I_c = -1 mA$
Emitter-base breakdown voltage	BV_{EBO}	-5	—	—	V	$I_E = -100 \mu A$
Collector cutoff current	I_{cbo}	—	—	-0.1	μA	$V_{CB} = -35V$
Emitter cutoff current	I_{EBO}	—	—	-0.1	μA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.4	V	$I_c/I_B = -150mA/-15mA$
		—	—	-0.75	V	$I_c/I_B = -500mA/-50mA$
Base-emitter saturation voltage	$V_{BE(sat)}$	-0.75	—	-0.95	V	$I_c/I_B = -150mA/-15mA$
		—	—	-1.3	V	$I_c/I_B = -500mA/-50mA$
DC current transfer ratio	h_{FE}	30	—	—	—	$V_{CE} = -1V, I_c = -0.1mA$
		60	—	—	—	$V_{CE} = -1V, I_c = -1mA$
		100	—	—	—	$V_{CE} = -1V, I_c = -10mA$
		100	—	300	—	$V_{CE} = -1V, I_c = -150mA$
		20	—	—	—	$V_{CE} = -2V, I_c = -500mA$
Gain bandwidth product	f_r	200	—	—	MHz	$V_{CE} = -10V, I_E = 20mA, f = 100MHz$
Collector output capacitance	C_{ob}	—	—	8.5	pF	$V_{CB} = -10V, f = 100kHz$
Emitter input capacitance	C_{ib}	—	—	30	pF	$V_{EB} = -0.5V, f = 100kHz$
Delay time	t_d	—	—	15	ns	$V_{CC} = -30V, V_{EB(OFF)} = -2V, I_c = -150mA, I_{B1} = -15mA$
Rise time	t_r	—	—	20	ns	$V_{CC} = -30V, V_{EB(OFF)} = -2V, I_c = -150mA, I_{B1} = -15mA$
Storage time	t_{stg}	—	—	225	ns	$V_{CC} = -30V, I_c = -150mA, I_{B1} = -I_{B2} = -15mA$
Fall time	t_f	—	—	30	ns	$V_{CC} = -30V, I_c = -150mA, I_{B1} = -I_{B2} = -15mA$

●Electrical characteristic curves

The electrical characteristic curves for these products are the same as those of UMT2907A, SST2907A, MMST2907A and PN2907A. Refer to pages 598 to 601.